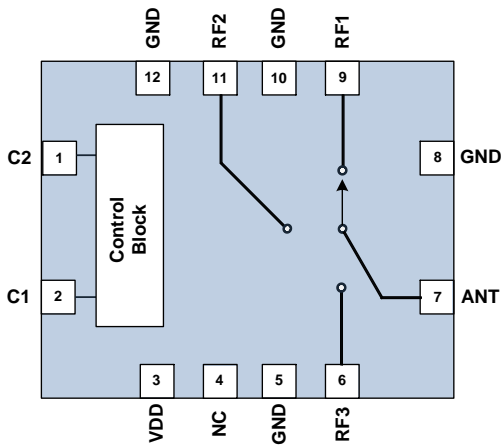


# RFSW6032

Low Insertion High Isolation SP3T Switch  
5MHz to 6000MHz

The RFSW6032 is a low loss, high isolation SP3T switch with performance optimized for use in Cellular BTS applications. It is also ideally suited for use in CATV and SATV applications. This part is packaged in a compact 1.8mm x 1.8mm, 12-pin, QFN package which allows for a small solution size with no need for external DC blocking capacitors (when no external DC is applied to the device ports).



Functional Block Diagram



Package: QFN, 12-pin,  
1.8mm x 1.8mm

## Features

- 5MHz to 6000MHz Operation
- Excellent Insertion Loss and Isolation Performance
  - Low Insertion Loss: 0.45dB at 2GHz
  - High Isolation: 37dBm at 2GHz
- High IP3: >70dBm at 2GHz
- Compatible with Low Voltage Logic ( $V_{HIGH}$  Minimum = 1.3V)
- No External DC Blocking
  - Capacitors Required on RF Paths if DC is Applied Externally
- 2000V HBM ESD Rating on All Ports
- 3V to 5V Operation

## Applications

- Cellular BTS
- CATV and SATV Applications
- Test Equipment
- General Purpose Switching

## Ordering Information

RFSW6032SQ	Sample bag with 25 pieces
RFSW6032SR	7" Reel with 100 pieces
RFSW6032TR7	7" Reel with 2500 pieces
RFSW6032PCK-410	5MHz to 6GHz PCBA with 5-piece sample bag

## Absolute Maximum Ratings

Parameter	Rating	Unit
Control Voltage ( $V_{CTL}$ )	3.0	V
Supply Voltage ( $V_{DD}$ )	6.0	V
Maximum CW Input Power for $V_{DD} = 3V$	35	dBm
Max Input Power During Active Switching	27	dBm
Storage Temperature Range	-40 to +150	°C
ESD Rating - Human Body Model (HBM)	2000	V
Moisture Sensitivity Level	MSL2	



**Caution!** ESD sensitive device.



RFMD Green: RoHS status based on EU Directive 2011/65/EU (at time of this document revision), halogen free per IEC 61249-2-21, < 1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

## Recommended Operating Condition

Parameter	Specification			Unit
	Min	Typ	Max	
Operating Temperature Range	-40		+85	°C
$V_{DD}$ – Switch Supply Voltage	3	5	5.5	V

## Nominal Operating Parameters

Parameter	Specification			Unit	Condition
	Min	Typ	Max		
General Performance					Electrical Specifications, TA = 25°C, VDD = 3V to 5V
Operating Frequency Range	5		6000	MHz	
Insertion Loss (RFC to RF1/RF2/RF3)		0.35	0.45	dB	925MHz
		0.45	0.6	dB	1990MHz
		0.5	0.7	dB	2650MHz
		1.2		dB	5850MHz
Isolation (RFC to RF1/RF2/RF3)		36		dB	925MHz
		29		dB	1990MHz
		26		dB	2650MHz
		15		dB	5850MHz
Isolation (RF1 to RF2/RF3)	35	40		dB	925MHz
	30	37		dB	1990MHz
		32		dB	2650MHz
		19		dB	5850MHz
Return Loss (RF1/RF2 On-state)		23		dB	5MHz ~ 3GHz
		14		dB	3GHz ~ 6GHz
900MHz Second Harmonic		-107	-85	dBc	Pin = 28dBm

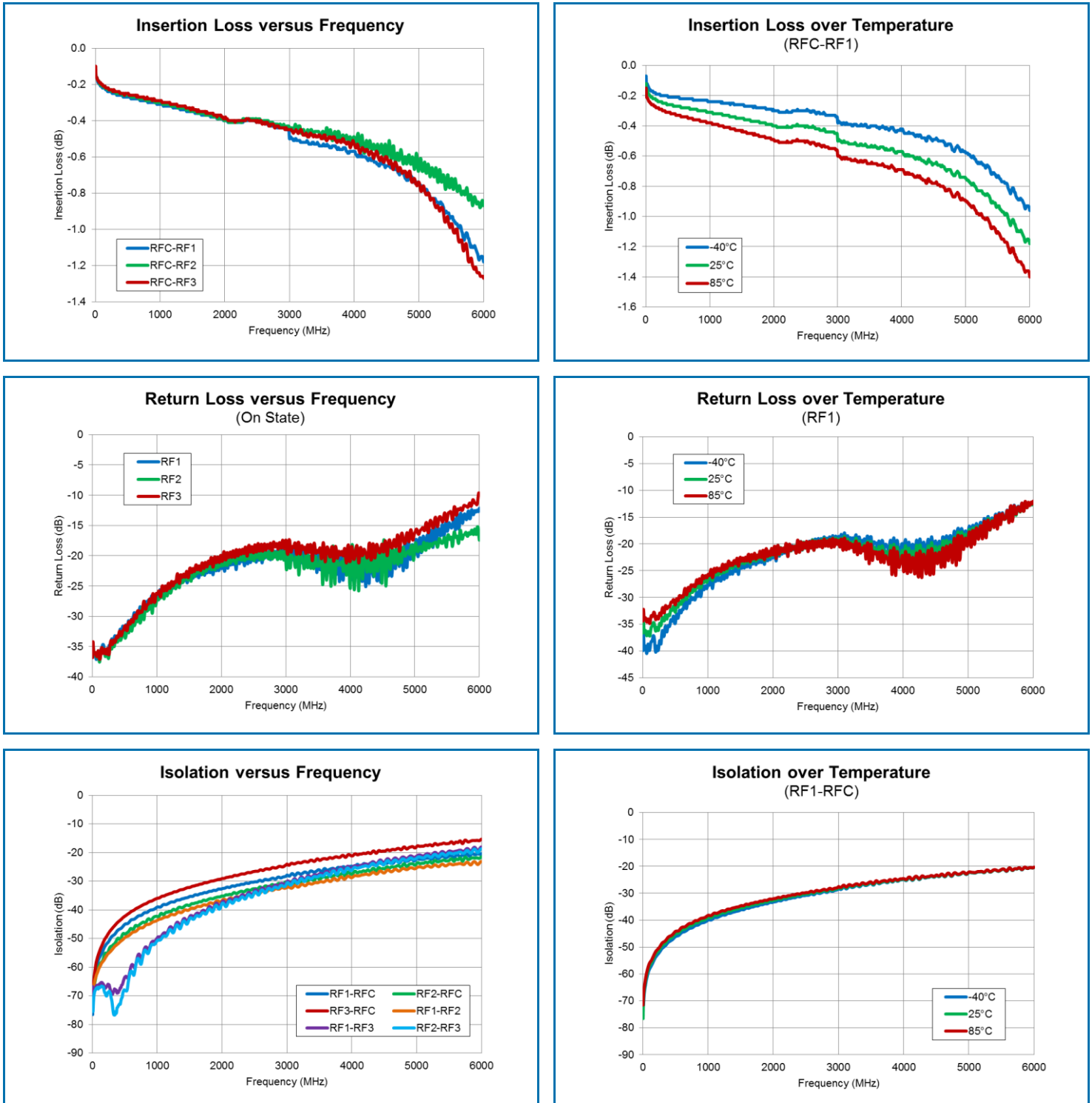
Parameter	Specification			Unit	Condition
	Min	Typ	Max		
<b>General Performance - Continued</b>					<b>Electrical Specifications, TA = 25°C, V<sub>DD</sub> = 3V to 5V</b>
900MHz Third Harmonic		-102	-85	dBc	Pin = 33dBm
2000MHz Second Harmonic		-99	-80	dBc	
2000MHz Third Harmonic		-90	-77	dBc	
Input IP3		70		dBm	2GHz, 21dBm per tone, 1MHz spacing
P1dB		>35		dBm	
Max Operational Input Power		35		dBm	
<b>Power Supply</b>					
V <sub>DD</sub> Supply Current		65	100	μA	
CTL1, CTL2 – Control Voltage High	1.3		2.7	V	
CTL1, CTL2 – Control Voltage Low	0		0.45	V	
Control Current			5	μA	
Switching Speed, One RF Port to Another		2	5	us	
Turn On Time		4	20	us	

## Power-up / Power-down Sequence and Operation Controls

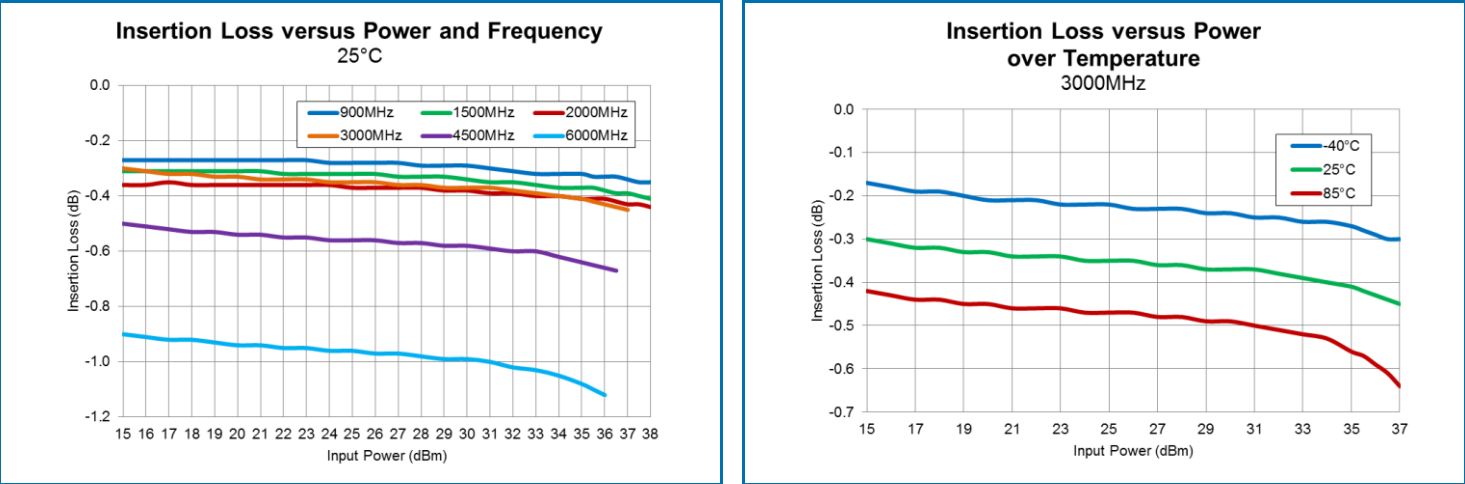
Power-up / Power-down	Sequence for Power-up and Power-down from Supply that is Connected to V <sub>DD</sub> Pin
Power-up	Turn on VDD, then C1 and C2, then (20μs or greater), apply RF signal
Power-down	Turn off RF signal, then C1 and C2, turn off V <sub>DD</sub>
Switching Ports	Turn off RF signal, then change C1 and C2 state, then (5μs or greater). Turn on RF signal

## Switch is controlled by C1 and C2

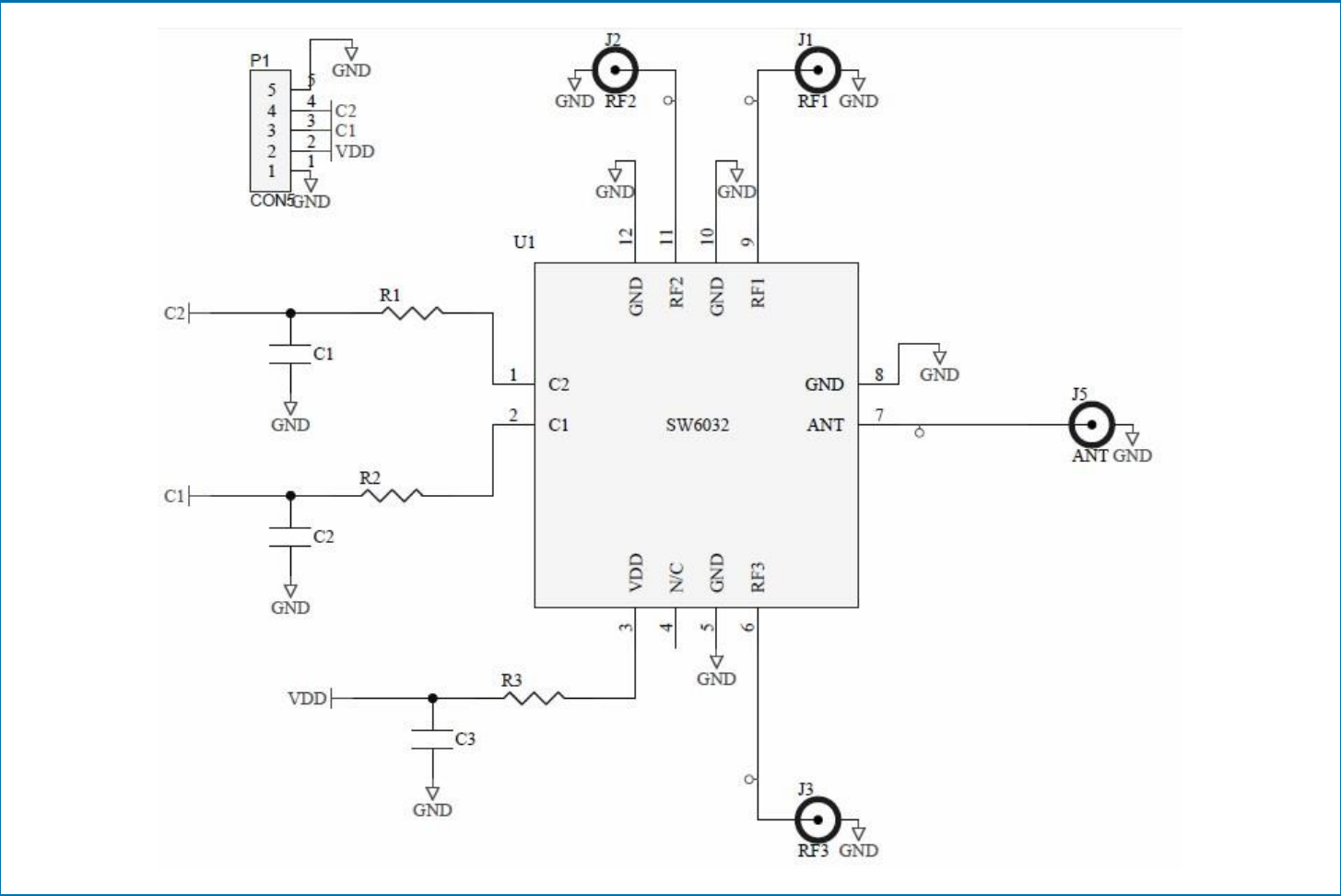
Mode	C1	C2
RF1-ANT	High	Low
RF2-ANT	Low	High
RF3-ANT	High	High

**Typical Performance:  $V_{DD} = 5V$  unless otherwise noted**


Typical Performance:  $V_{DD} = 5V$  unless otherwise noted



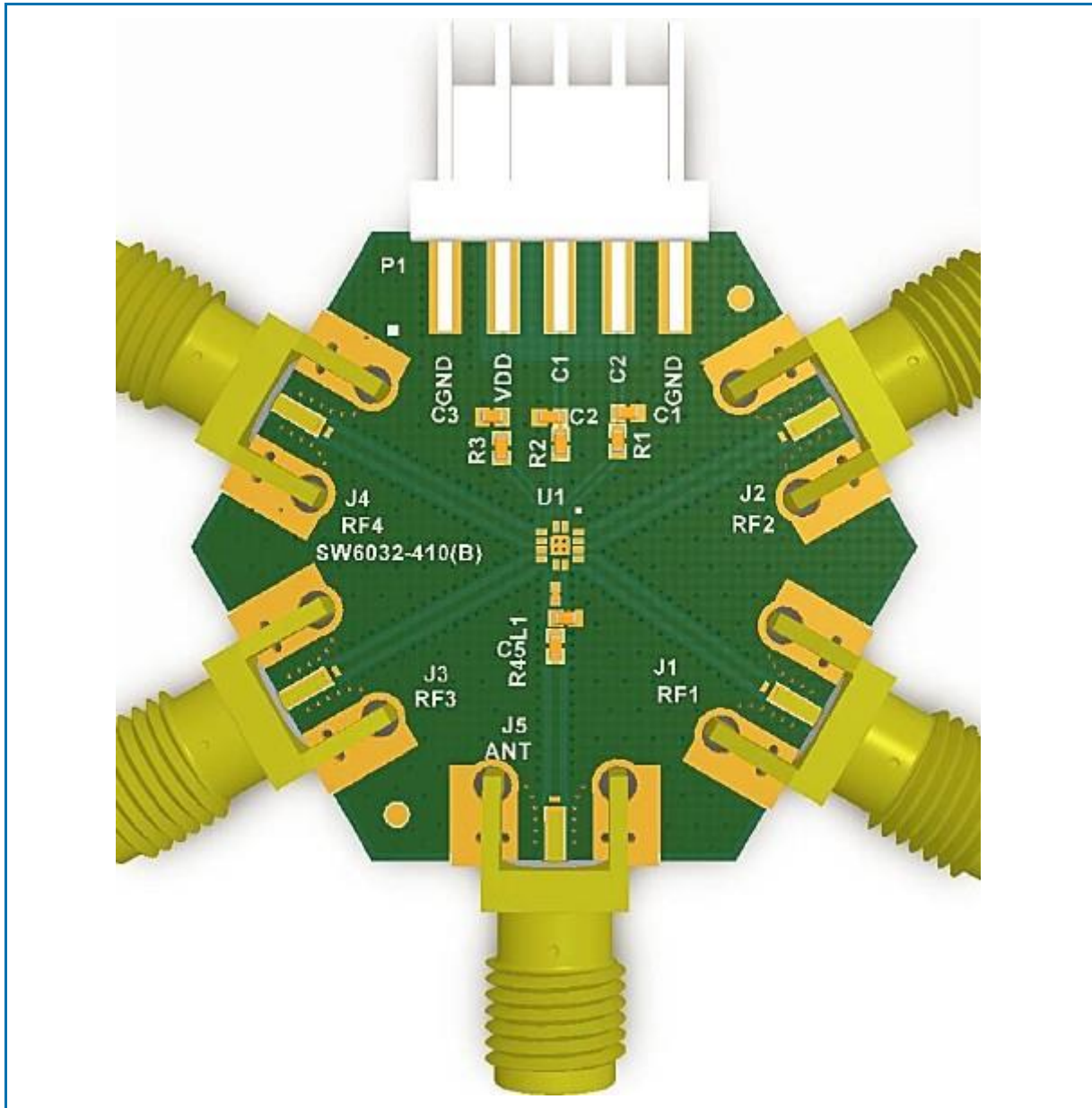
Evaluation Board Schematic 5MHz to 6000MHz Application Circuit



Evaluation Board Bill of Materials (BOM) 5MHz to 6000MHz Application Circuit

Description	Reference Designator	Manufacturer	Manufacturer's P/N
SW6032 Evaluation Board			RFSW6032-410
CAP, 100pF, 5%, 50V, C0G, 0402	C1-C2	Murata Electronics	GRM155C1H101JA01D
CAP, 10000pF, 10%, 25V, X7R, 0402	C3	Murata Electronics	GRM155R71E103KA01D
RES, 0Ω, 0402	R1-R3	Kamaya, Inc.	RMD1/16SJPTH
CONN, SMA, END LNCH, MINI, FLT, 0.068"	J1-J3, J5	Emerson Network Power	142-0741-851
CONN, HDR, ST, PLRZD, 5-PIN, 0.100"	P1	ITW Pancon	MPSS100-5-C
High Power SP3T	U1	RFMD	RFSW6032

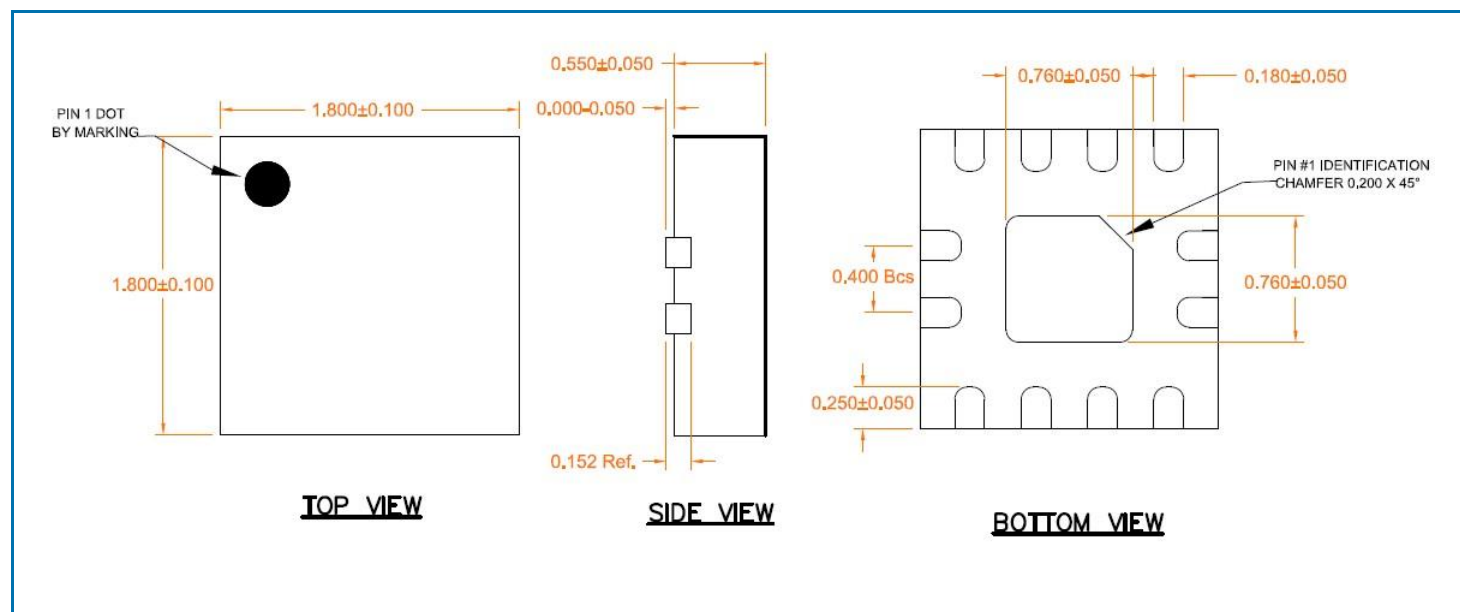
## Evaluation Board Assembly Drawing



## Pin Names and Descriptions

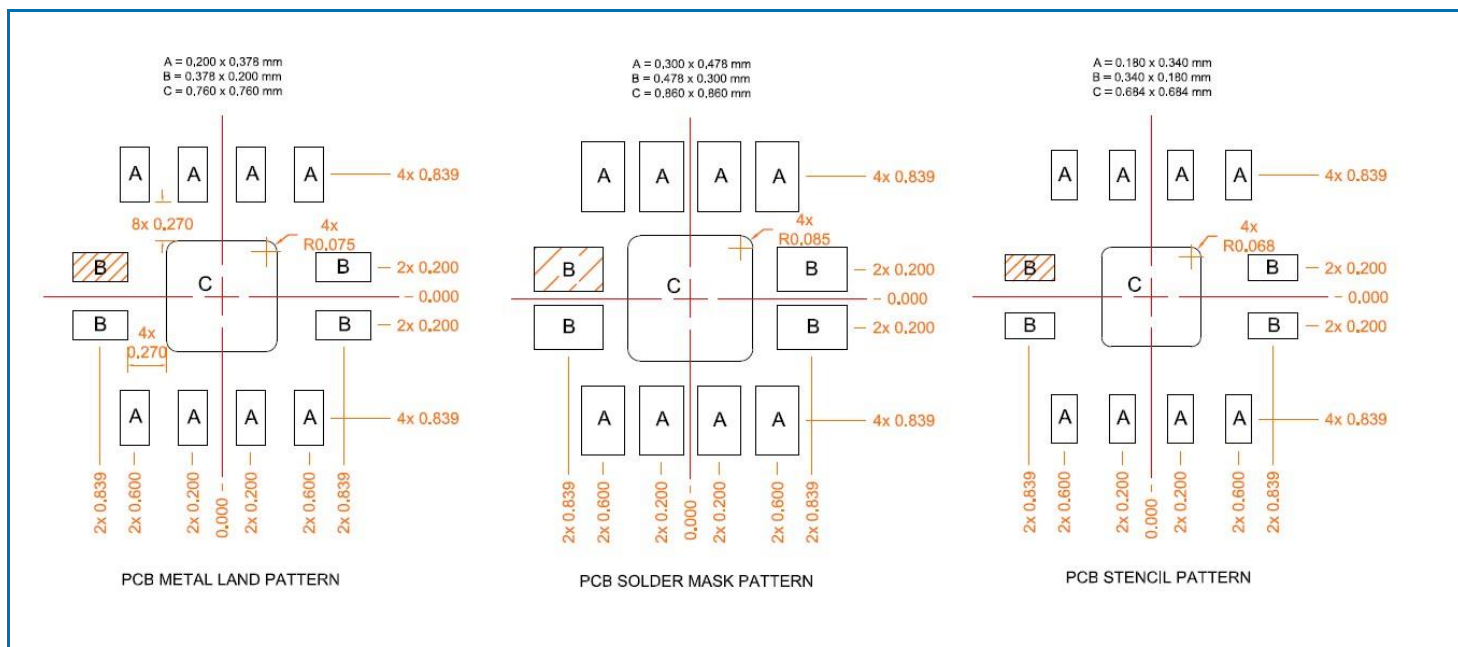
Pin	Name	Description
1	C2	Switch Logic Control 2
2	C1	Switch Logic Control 1
3	VDD	Supply Voltage
4	NC	Not Connected
5	GND	Low Inductance Path to Ground
6	RF3	Single-ended RF Port
7	ANT	Single-ended RF Port
8	GND	Low Inductance Path to Ground
9	RF1	Single-ended RF Port
10	GND	Low Inductance Path to Ground
11	RF2	Single-ended RF Port
12	GND	Low Inductance Path to Ground

## Package Outline Drawing (Dimensions in millimeters)





## Stencil, PCB Pattern (Dimensions in millimeters)



## Branding Diagram

